Seat No.:	Enrolment No.
3Cat 110	Lindincht 110.

GUJARAT TECHNOLOGICAL UNIVERSITY

		BE - SEMESTER-I (NEW) EXAMINATION – WINTER 2023	
	Sul	bject Code:3110016 Date:25-01-2024	
	Sul	oject Name:Basic Electronics	
	Tin	ne:02:30 PM TO 05:00 PM Total Marks:70	
	Inst	 Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks. Simple and non-programmable scientific calculators are allowed. 	MARKS
Q.1	(a)	Draw symbol and truth table for AND, NOR, EX-OR logic gates.	03
	(b)	Discuss forward and reverse bias operation of a P-N junction diode with depletion region.	04
	(c)	Draw CB configuration and discuss its input and output characteristics with $I_{CBO},\ r_i,\ r_o,$ and current gain $\alpha.$	07
Q.2	(a)	Describe Negative clamper circuit with necessary waveforms	03
	(b)	Describe RC filter with its limitations.	04
	(c)	Draw circuit diagram of Center-taped full wave rectifier and explain its operation with necessary waveforms and derivation of $V_{\rm dc}$.	07
		OR	
	(c)	Describe diode approximations in detail.	07
Q.3	(a)	Draw circuit for Voltage doubler and explain its operation.	03
	(b)	Briefly explain the effect of coupling capacitor and bypass capacitor on small signal transistor amplifier.	04
	(c)	Draw circuit for Emitter feedback bias and explain in detail with its advantages and disadvantages.	07
		OR	
Q.3	(a)	State the difference between Avalanche breakdown and Zener breakdown.	03
	(b)	Discuss Zener diode as voltage regulator.	04
	(c)	Discuss load line, Q point, DC & AC load lines for BJT.	07
Q.4	(a)	Derive relation between α & β for BJT.	03
	(b)	Compare different BJT configurations.	04
	(c)	Describe working principle and applications of PIN Photo diode and Solar cell. OR	07
Q.4	(a)	Briefly explain regions of operation for BJT.	03
	(b)	Discuss seven segment displays with its types.	04
	(c)	Draw CE configuration and discuss its input and output characteristics with I _{CEO} , r _i ,	07

 r_o , and current gain β .

Q.5	(a)	Compare FET with BJT.	03
	(b)	Explain FET as a switch.	04
	(c)	State different logic families and compare them in terms of fan in, fan out, propagation	07
		delay, noise margin, power dissipation.	
		OR	
Q.5	(a)	Construct AND & OR gates with diodes.	03
	(b)	Explain FET as an amplifier.	04
	(c)	Explain Drain characteristics and Transfer characteristics of JFET in detail with all related terms as Transconductance g_m , drain resistance r_d , and amplification factor μ .	07
